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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC2545, 2SC2546, 2SC2547

Silicon NPN Epitaxial

RENESAS

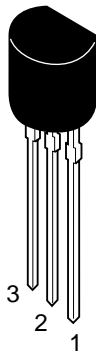
ADE-208-1067A (Z)
2nd. Edition
Mar. 2001

Application

- Low frequency low noise amplifier

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SC2545, 2SC2546, 2SC2547

Absolute Maximum Ratings (Ta = 25°C)

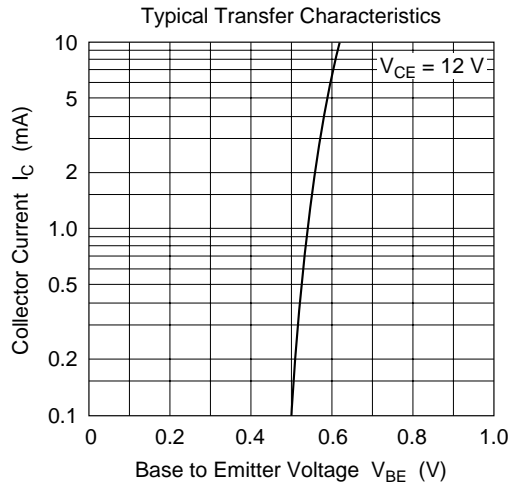
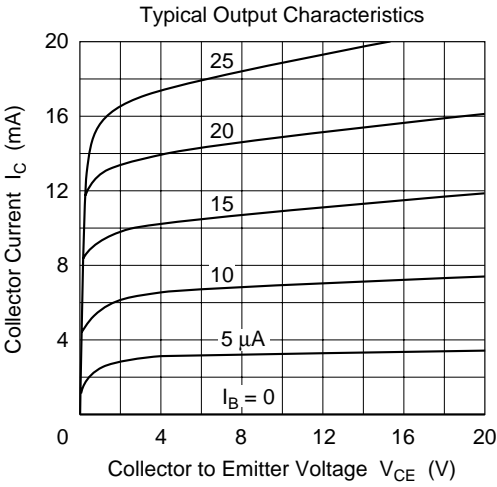
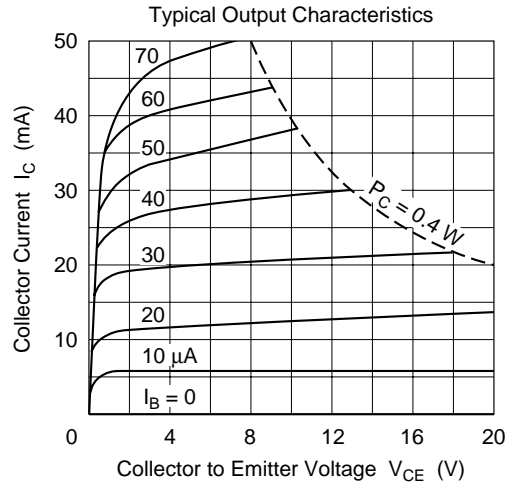
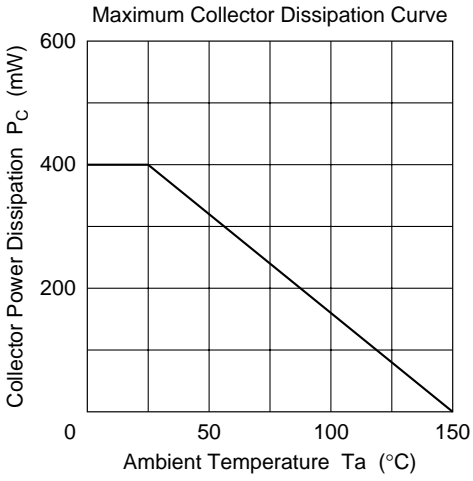
Item	Symbol	2SC2545	2SC2546	2SC2547	Unit
Collector to base voltage	V _{CBO}	60	90	120	V
Collector to emitter voltage	V _{CEO}	60	90	120	V
Emitter to base voltage	V _{EBO}	5	5	5	V
Collector current	I _C	100	100	100	mA
Emitter current	I _E	-100	-100	-100	mA
Collector power dissipation	P _C	400	400	400	mW
Junction temperature	T _j	150	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	-55 to +150	°C

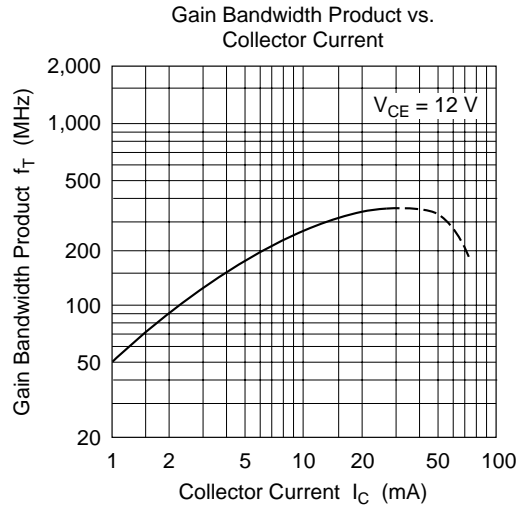
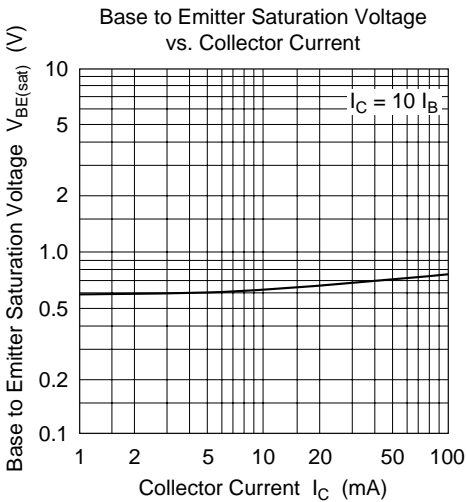
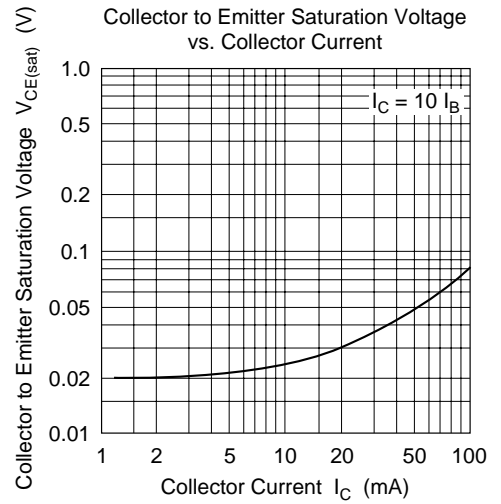
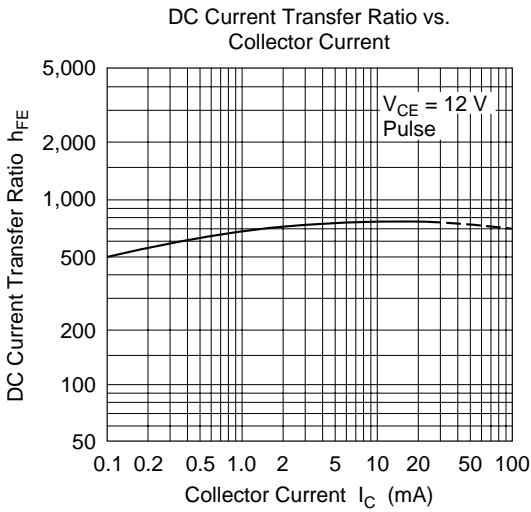
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SC2545			2SC2546			2SC2547			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	—	—	90	—	—	120	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	—	—	90	—	—	120	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	—	—	0.1	—	—	0.1	μA	$V_{CB} = 50 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	—	—	0.1	—	—	0.1	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	1200	250	—	1200	250	—	800		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	—	—	0.2	—	—	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	—	0.6	—	—	0.6	—	—	0.6	—	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Gain bandwidth product	f_T	—	90	—	—	90	—	—	90	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.0	—	—	3.0	—	—	3.0	—	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Noise voltage referred input	e_n	—	0.5	—	—	0.5	—	—	0.5	—	nV/ $\sqrt{\text{Hz}}$	$V_{CE} = 6 \text{ V}, I_C = 10 \text{ mA}, f = 1 \text{ kHz}, R_g = 0, \Delta f = 1 \text{ Hz}$

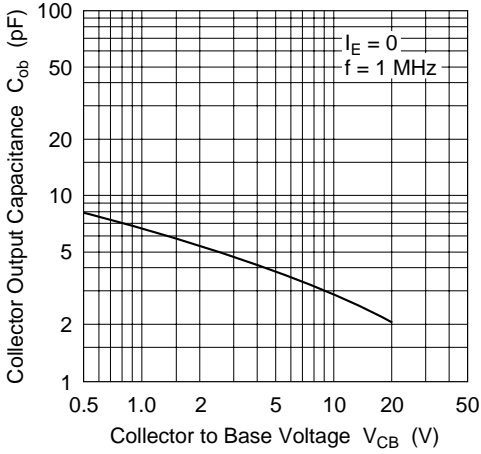
Note: 1. The 2SC2545, 2SC2546 and 2SC2547 are grouped by h_{FE} as follows.

	D	E	F
2SC2545, 2SC2546	250 to 500	400 to 800	600 to 1200
2SC2547	250 to 500	400 to 800	—

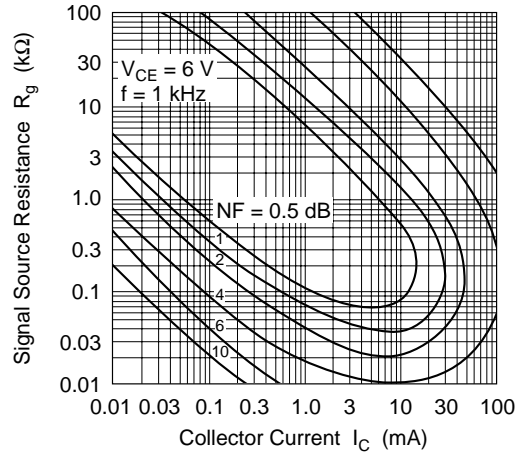




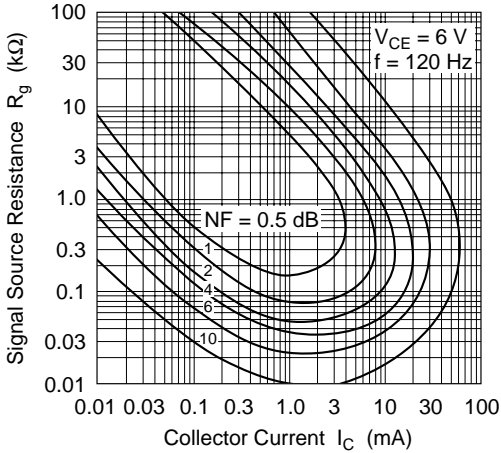
Collector Output Capacitance vs. Collector to Base Voltage



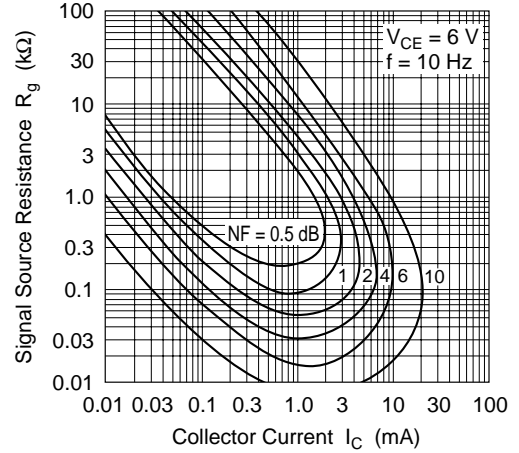
Contours of Constant Noise Figure



Contours of Constant Noise Figure



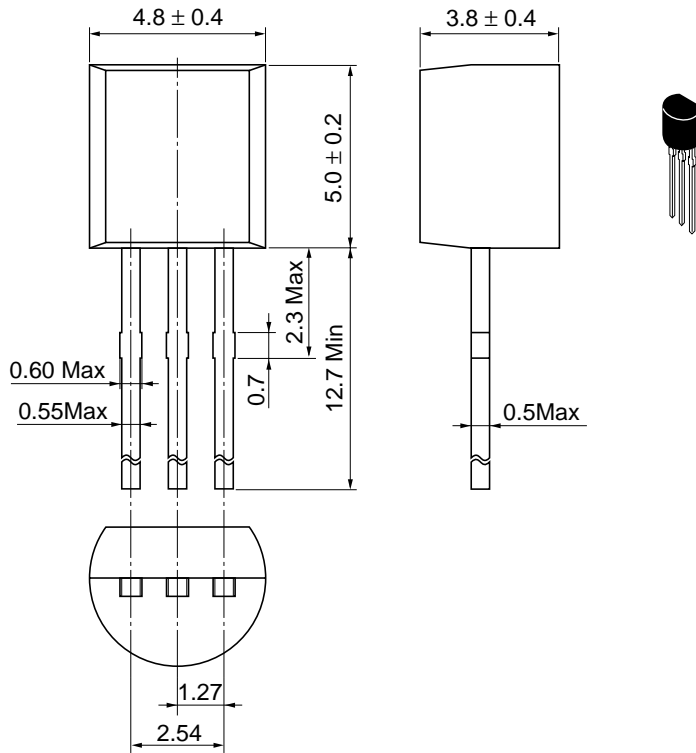
Contours of Constant Noise Figure



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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